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Technology and Applications VIII***

Mark S. Zediker
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Contents

- ix *Conference Committee*
- xi *Ultrafast fiber laser technology: status and prospects (Plenary Paper) [7579-102]*
A. Tünnermann, J. Limpert, Friedrich-Schiller-Univ. Jena (Germany) and Fraunhofer-Institute for Applied Optics and Precision Engineering (Germany)

SESSION 1 LASER DIODE RELIABILITY

- 7583 02 **Reliability of high performance 9xx-nm single emitter laser diodes** [7583-01]
L. Bao, J. Wang, M. DeVito, D. Xu, D. Wise, P. Leisher, M. Grimshaw, W. Dong, S. Zhang, K. Price, D. Li, C. Bai, S. Patterson, R. Martinsen, nLIGHT Corp. (United States)
- 7583 03 **Highly reliable 637-639-nm red high-power LDs for displays** [7583-02]
T. Nishida, N. Shimada, K. Ono, T. Yagi, A. Shima, Mitsubishi Electric Corp. (Japan)
- 7583 04 **Reliability of high-power QCW arrays** [7583-03]
R. Feeler, J. Junghans, J. Remley, D. Schnurbusch, E. Stephens, Northrop Grumman Cutting Edge Optronics (United States)
- 7583 05 **Reliability and performance of 808-nm single emitter multi-mode laser diodes** [7583-04]
J. Wang, L. Bao, M. DeVito, D. Xu, D. Wise, M. Grimshaw, W. Dong, S. Zhang, C. Bai, P. Leisher, D. Li, H. Zhou, S. Patterson, R. Martinsen, J. Haden, nLIGHT Corp. (United States)
- 7583 06 **Reliable operation of 8xx mini-bar-based hermetic modules** [7583-05]
X. Jin, S. Cutillas, D. Liu, E. Wolak, S.-K. Park, K. Johnson, T. Towe, D. Lenarduzzi, T. Nguyen, T. Truchan, J. Mott, J. Harrison, Oclaro, Inc. (United States); A. Guarino, J. Müller, S. Pawlik, B. Sverdlov, N. Lichtenstein, Oclaro Switzerland AG (Switzerland); C. Button, Oclaro Technology plc (United Kingdom)
- 7583 07 **Root cause investigation of catastrophic degradation in high power multi-mode InGaAs-AlGaAs strained quantum well lasers** [7583-06]
Y. Sin, N. Ives, N. Presser, S. C. Moss, The Aerospace Corp. (United States)

SESSION 2 LASER DIODE MODULES I

- 7583 08 **High brightness fiber-coupled pump laser development** [7583-07]
K. Price, S. Karlsen, P. Leisher, R. Martinsen, nLIGHT Corp. (United States)
- 7583 09 **Roadmap to low cost high brightness diode laser power out of the fiber** [7583-08]
D. Schröder, E. Werner, A. Franke, L. Wagner, G. Bonati, JENOPTIK Laserdiode GmbH (Germany); F. Dörfel, H. Ziemer, A. Liem, T. Gabler, JT Optical Engine GmbH + Co. KG (Germany)

- 7583 0A **High-brightness 9XX-nm pumps with wavelength stabilization** [7583-09]
V. Gapontsev, N. Moshegov, P. Trubenko, A. Komissarov, I. Berishev, O. Raisky, N. Strougov, V. Chuyanov, O. Maksimov, A. Ovtchinnikov, IPG Photonics Corp. (United States)
- 7583 0B **Dramatic advances in direct diode lasers** [7583-10]
D. Havrilla, TRUMPF Inc. (United States); M. Holzer, R. Brockmann, S. Strohmaier, TRUMPF Laser GmbH & Co. KG (Germany)

SESSION 3 LASER DIODE MODULES II

- 7583 0C **High duty cycle hard soldered kilowatt laser diode arrays** [7583-11]
G. Klumel, Y. Karni, J. Oppenheim, Y. Berk, M. Shamay, R. Tessler, S. Cohen, SemiConductor Devices (Israel)
- 7583 0D **Micro-optic solutions for beam shaping of individually addressable high-power single-mode diode laser arrays** [7583-12]
M. Forrer, D. Kura, E. Langenbach, FISBA OPTIK AG (Switzerland)
- 7583 0E **KW-class industrial diode lasers comprised of single emitters** [7583-13]
K. Price, F. Pfeffer, P. Leisher, S. Karlsen, R. Martinsen, nLIGHT Corp. (United States)
- 7583 0F **High-power diode laser modules from 410 nm to 2200 nm** [7583-14]
B. Köhler, H. Kissel, M. Flament, P. Wolf, T. Brand, J. Biesenbach, DILAS Diodenlaser GmbH (Germany)
- 7583 0G **Fiber coupling of high-power diode laser stack for direct polycarbonate processing** [7583-15]
E. Vidal, I. Quintana, U. Azkorbebeitia, Fundacion Tekniker (Spain); E. Mendez, G. Viera, M. Galán, MONOCROM S.L. (Spain); D. Otaduy, Fundacion Tekniker (Spain)

SESSION 4 LASER DIODE HEAT REMOVAL

- 7583 0H **Expansion matched heat sinks made by μ -metal injection molding** [7583-16]
M. Leers, E. Liermann, Fraunhofer Institute for Laser Technology (Germany); P. Imgrund, L. Kramer, J. Volkert, Fraunhofer Institute for Manufacturing & Advanced Materials (Germany)
- 7583 0I **Simple method for modeling thermoelectric cooler (TEC) performance of single-emitter semiconductor-laser packages with concentrated heat sources** [7583-17]
J. Du, M. Au, L. Zavala, P. Yalamanchili, J. Skidmore, E. Zucker, JDSU (United States)
- 7583 0J **Development of asymmetric epitaxial structures for 65% efficiency laser diodes in the 9xxnm range** [7583-50]
M. Levy, Y. Karni, N. Rapaport, Y. Don, Y. Berk, D. Yanson, S. Cohen, J. Oppenheim, SemiConductor Devices (Israel)
- 7583 0K **Progress in the development of active heat sink for high-power laser diodes** [7583-19]
J. Vetovec, Aqwest LLC (United States); R. Feeler, S. Bonham, Northrop-Grumman Cutting Edge Optronics (United States)

SESSION 5 LASER DIODE DEVICES I

- 7583 OL **Recent development of high-power-efficiency 50-W CW TE/TM polarized 808-nm diode laser bar at Lasertel** [7583-20]
C. Cao, L. Fan, I. Ai, J. Li, B. Caliva, L. Zeng, P. Thiagarajan, M. McElhinney, Lasertel, Inc. (United States)
- 7583 OM **Extending the wavelength range in the Oclaro high-brightness broad area modules** [7583-21]
S. Pawlik, A. Guarino, B. Sverdlov, J. Müller, Oclaro Switzerland AG (Switzerland); C. Button, Oclaro Technology, plc (United Kingdom); S. Arlt, D. Jaeggi, N. Lichtenstein, Oclaro, Switzerland AG (Switzerland)
- 7583 ON **975-nm high-power broad area diode lasers optimized for narrow spectral linewidth applications** [7583-22]
P. Crump, C. M. Schultz, A. Pietrzak, S. Knigge, O. Brox, A. Maaßdorf, F. Bugge, H. Wenzel, G. Ebert, Ferdinand-Braun-Institut für Höchstfrequenztechnik (Germany)
- 7583 OO **Mid-infrared high-power diode lasers and modules** [7583-23]
M. T. Kelemen, J. Gilly, m2k-laser GmbH (Germany); M. Rattunde, J. Wagner, Fraunhofer-Institut für Angewandte Festkörperphysik (Germany); S. Ahlert, J. Biesenbach, DILAS Diodenlaser GmbH (Germany)
- 7583 OP **High temperature and high peak-power 808-nm QCW bars and stacks** [7583-24]
G. Bacchin, Intense Ltd. (United Kingdom); A. Fily, Intense-US (United States); B. Qiu, D. Fraser, S. Robertson, Intense Ltd. (United Kingdom); V. Loyo-Maldonado, Intense-US (United States); S. D. McDougall, B. Schmidt, Intense Ltd. (United Kingdom)
- 7583 OQ **Eye safe high power laser diode in the 1410-1550-nm range** [7583-25]
J. Boucart, Oclaro Switzerland AG (Switzerland); B. de Largy, M. Kearley, Oclaro Technology plc (United Kingdom); N. Lichtenstein, Oclaro Switzerland AG (Switzerland)

SESSION 6 LASER DIODE DEVICES II

- 7583 OR **High power DFB laser diodes** [7583-26]
W. Zeller, nanoplus GmbH (Germany); M. Kamp, Julius-Maximilians-Univ. Würzburg (Germany); J. Koeth, nanoplus GmbH (Germany)
- 7583 OS **Comparison of concepts for high-brightness diode lasers at 976 nm** [7583-27]
J. Gilly, P. Friedmann, m2k-laser GmbH (Germany); H. Kissel, J. Biesenbach, DILAS Diodenlaser GmbH (Germany); M. T. Kelemen, m2k-laser GmbH (Germany)
- 7583 OT **Scaling brilliance of high power laser diodes** [7583-28]
H. König, G. Grönninger, C. Lauer, W. Reill, M. Arzberger, U. Strauß, OSRAM Opto Semiconductors GmbH (Germany); H. Kissel, J. Biesenbach, DILAS Diodenlaser GmbH (Germany); A. Kösters, J. Malchus, V. Krause, Laserline GmbH (Germany)
- 7583 OU **JENOPTIK diode lasers and bars optimized for high-power applications in the NIR range** [7583-29]
M. Zorn, R. Hülsewede, H. Schulze, J. Sebastian, JENOPTIK Diode Lab GmbH (Germany); P. Hennig, D. Schröder, JENOPTIK Laserdiode GmbH (Germany)

SESSION 7 LASER DIODE DEVICES III

7583 0V **High-brightness 635-nm tapered diode lasers with optimized index guiding** [7583-30]
D. Feise, G. Blume, H. Dittrich, C. Kaspari, K. Paschke, G. Erbert, Ferdinand-Braun-Institut für
Höchstfrequenztechnik (Germany)

7583 0W **Characteristics of red-emitting broad area stripe laser diodes with zinc diffused window
structures** [7583-31]
T. Ohno, M. Takiguchi, K. Wakabayashi, H. Uchida, K. Naganuma, M. Ohara, S. Ito, S. Hirata,
Sony Corp. (Japan)

SESSION 8 BEAM COMBINING

7583 0Y **Demonstration of high pointing accuracy dual-axis collimation of 49 emitter diode bar using
a laser-written custom phase-plate** [7583-33]
N. Trela, H. J. Baker, Heriot-Watt Univ. (United Kingdom); J. J. Wendland, PowerPhotonic, Ltd.
(United Kingdom); D. R. Hall, Heriot-Watt Univ. (United Kingdom)

7583 0Z **Coherent beam combining of high-power broad-area laser diode array in CW and pulsed
modes** [7583-34]
B. Liu, Y. Liu, Y. Braiman, Oak Ridge National Lab. (United States)

7583 10 **Progress in high-brightness diode laser development based on tailored diode laser bars**
[7583-35]
S. D. Roh, D. M. Grasso, N. Shou, R. Pathak, G. Cheung, D. Schleuning, T. Hasenberg,
Coherent, Inc. (United States)

7583 11 **Coherent polarization locking of a diode emitter array** [7583-36]
S. P. Ng, Nanyang Technological Univ. (Singapore); P. B. Phua, Nanyang Technological Univ.
(Singapore) and DSO National Labs. (Singapore)

7583 12 **High-brightness emission from stripe-array broad area diode lasers operated in off-axis
external cavities** [7583-37]
A. Jechow, D. Skoczowsky, Univ. of Potsdam (Germany); M. Lichtner, M. Radziunas,
Weierstrass Institute for Applied Analysis and Stochastics (Germany); R. Menzel, Univ. of
Potsdam (Germany)

7583 13 **250W diode laser for low pressure Rb vapor pumping** [7583-38]
A. Podvyaznyy, G. Venus, CREOL, The College of Optics and Photonics, Univ. of Central
Florida (United States); V. Smirnov, O. Mokhun, V. Koulechov, OptiGrate Corp. (United
States); D. Hostutler, Air Force Research Lab. (United States); L. Glebov, CREOL, The College
of Optics and Photonics, Univ. of Central Florida (United States)

SESSION 9 POSTER SESSION

- 7583 14 **Degradation analysis of individual emitters in 808-nm QCW laser diode array for space applications** [7583-40]
O. Rehioui, IMS-Labs., CNRS, Univ. Bordeaux (France) and Quantel Laser Diodes (France); L. Bechou, IMS-Labs., CNRS, Univ. Bordeaux (France); T. Fillardet, A. Kohl, Quantel Laser Diodes (France); Y. Ousten, IMS-Labs., CNRS, Univ. Bordeaux (France); G. Volluet, Quantel Laser Diodes (France)
- 7583 17 **High-power distributed-feedback tapered master-oscillator power amplifiers emitting at 1064 nm** [7583-43]
D. Jedrzejczyk, O. Brox, F. Bugge, J. Fricke, A. Ginolas, K. Paschke, H. Wenzel, G. Erbert, Ferdinand-Braun-Institut für Höchstfrequenztechnik (Germany)
- 7583 18 **CW to QCW power scaling of high-power laser bars** [7583-44]
J. Müller, R. Todt, M. Krejci, Y. Manz-Gilbert, B. Valk, R. Brunner, R. Bättig, N. Lichtenstein, Oclaro Switzerland AG (Switzerland)
- 7583 19 **1043-nm semiconductor disk laser** [7583-45]
Y. Song, P. Zhang, J. Tian, X. Zhang, Beijing Univ. of Technology (China)
- 7583 1A **High-power high-brightness 808-nm QCW laser diode mini bars** [7583-46]
H. Huang, J. Wang, M. DeVito, L. Bao, A. Hodges, S. Zhang, D. Wise, M. Grimshaw, D. Xu, C. Bai, nLIGHT Corp. (United States)
- 7583 1E **Laser-assisted shearing: new application for high-power diode lasers** [7583-53]
M. Emonts, C. Brecher, Fraunhofer-Institut für Produktionstechnologie (Germany)

Author Index

Conference Committee

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- 1 Laser Diode Reliability
Robert J. Martinsen, nLIGHT Corporation (United States)
- 2 Laser Diode Modules I
Erik P. Zucker, JDSU (United States)
- 3 Laser Diode Modules II
Friedrich G. Bachmann, Rofin-Sinar Laser GmbH (Germany)
- 4 Laser Diode Heat Removal
Stefan W. Heinemann, Fraunhofer USA, Inc. (United States)

- 5 Laser Diode Devices I
Erik P. Zucker, JDSU (United States)
- 6 Laser Diode Devices II
Kurt J. Linden, Spire Corporation (United States)
- 7 Laser Diode Devices III
Kurt J. Linden, Spire Corporation (United States)
- 8 Beam Combining
Volker K. Krause, Laserline GmbH (Germany)